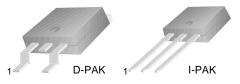


### **KSH112**

### **D-PAK for Surface Mount Applications**

- High DC Current Gain
- Built-in a Damper Diode at E-C
- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I-PAK, " I " Suffix)
- Electrically Similar to Popular TIP112

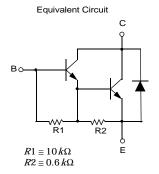


1.Base 2.Collector 3.Emitter

## **NPN Silicon Darlington Transistor**

### **Absolute Maximum Ratings** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	2	Α
I <sub>CP</sub>	Collector Current (Pulse)	4	Α
I <sub>B</sub>	Base Current	50	mA
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	20	W
	Collector Dissipation (T <sub>a</sub> =25°C)	1.75	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C



### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage	$I_C = 30 \text{mA}, I_B = 0$	100		V
I <sub>CEO</sub>	Collector Cut-off Current	$V_{CE} = 50V, I_{B} = 0$		20	μΑ
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 100V, I_B = 0$		20	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$		2	mA
h <sub>FE</sub>	* DC Current Gain	$V_{CE} = 3V, I_{C} = 0.5A$	500		
		$V_{CE} = 3V, I_{C} = 2A$	1000	12K	
		$V_{CE} = 3V$ , $I_C = 4A$	200		
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_{C} = 2A, I_{B} = 8mA$		2	V
		$I_C = 4A, I_B = 40mA$		3	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_C = 4A, I_B = 40mA$		4	V
V <sub>BE</sub> (on)	* Base-Emitter On Voltage	$V_{CE} = 3A$ , $I_C = 2A$		2.8	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.75A$	25		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_{E} = 0$		100	pF
		f = 0.1MHz			

<sup>\*</sup> Pulse Test: PW≤300μs, Duty Cycle≤2%

# **Typical Characteristics**

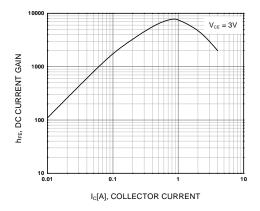


Figure 1. DC current Gain

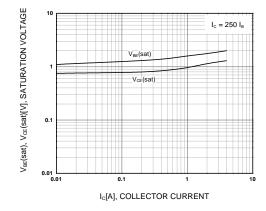


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

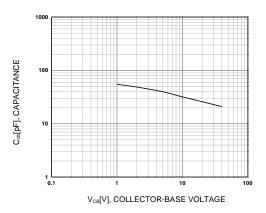


Figure 3. Collector Output Capacitance

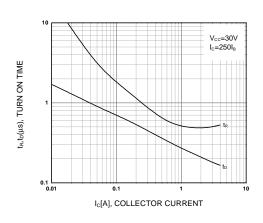


Figure 4. Turn On Time

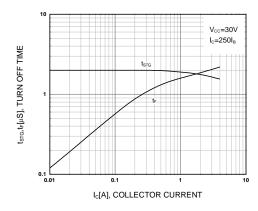


Figure 5. Turn Off Time

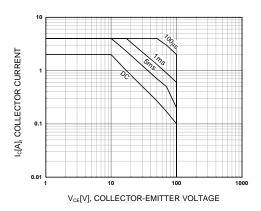


Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

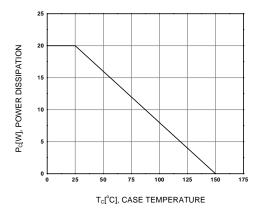
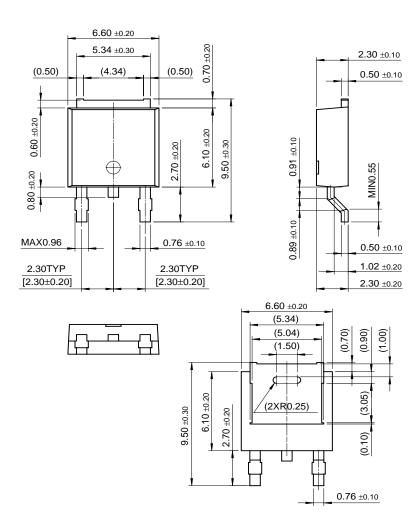


Figure 7. Power Derating

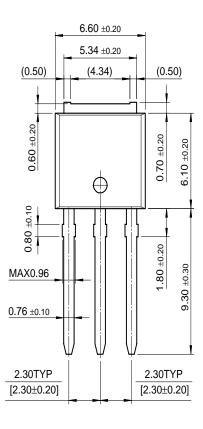
## **Package Dimensions**

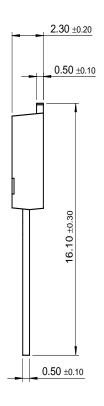
## D-PAK

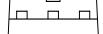


## Package Dimensions (Continued)

## I-PAK







Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
$CROSSVOLT^{TM}$	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board. Around the world.™		OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX <sup>TM</sup>
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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